





	°C					
	°C					
	°C					
	°C					
	°C					
	°C					
	°C					
	°C					

			±		

FIG.1: Power dissipation vs. on-state current

(per thyristor or diode)

$P_{T(AV)}/P_{F(AV)}(W)$

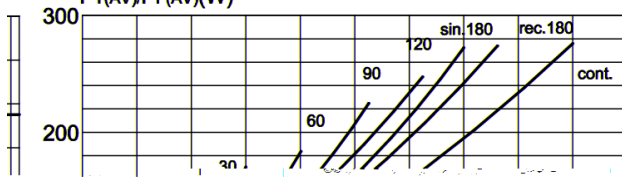


FIG.2: Maximum transient thermal impedance

junction to case(per thyristor or diode)

$R_{th(j-c)}(^{\circ}C/W)$

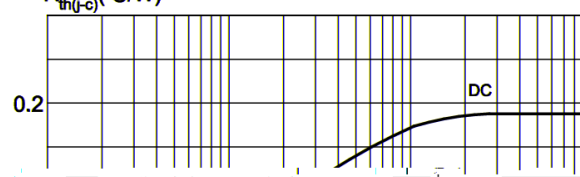


FIG.5 Gate trigger characteristics

$V_G(V)$

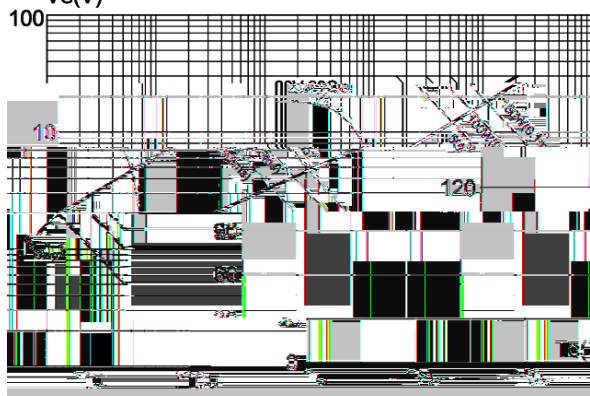


FIG.6: Forward current vs. case temperature

$I_{F(AV)}(A)$ (per thyristor or diode)

